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March 2015

FDD86102LZ

N-Channel Shielded Gate PowerTrench[®] MOSFET

100 V, 35 A, 22.5 mΩ

Features

- Shielded Gate MOSFET Technology
- Max $r_{DS(on)}$ = 22.5 mΩ at $V_{GS} = 10$ V, $I_D = 8$ A
- Max $r_{DS(on)}$ = 31 mΩ at $V_{GS} = 4.5$ V, $I_D = 7$ A
- HBM ESD protection level > 6 kV typical (Note 4)
- Very low Q_g and Q_{gd} compared to competing trench technologies
- Fast switching speed
- 100% UIL tested
- RoHS Compliant

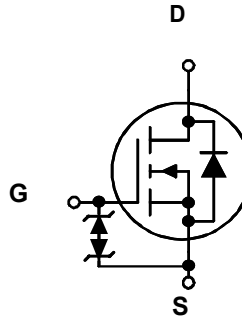
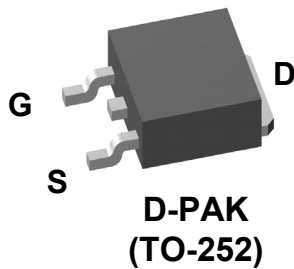


General Description

This N-Channel MOSFET is produced using Fairchild Semiconductor's advanced PowerTrench[®] process that incorporates Shielded Gate technology. This process has been optimized for the on-state resistance and switching loss. G-S zener has been added to enhance ESD voltage level.

Applications

- DC - DC Conversion
- Inverter
- Synchronous Rectifier



MOSFET Maximum Ratings $T_C = 25$ °C unless otherwise noted

| Symbol | Parameter | Rated | Units |
|----------------|--|-------------|-------|
| V_{DS} | Drain to Source Voltage | 100 | V |
| V_{GS} | Gate to Source Voltage | ±20 | V |
| I_D | Drain Current -Continuous $T_C = 25$ °C | 35 | A |
| | -Continuous $T_A = 25$ °C (Note 1a) | 8 | |
| | -Pulsed | 40 | |
| E_{AS} | Single Pulse Avalanche Energy (Note 3) | 84 | mJ |
| P_D | Power Dissipation $T_C = 25$ °C | 54 | W |
| | Power Dissipation $T_A = 25$ °C (Note 1a) | 3.1 | |
| T_J, T_{STG} | Operating and Storage Junction Temperature Range | -55 to +150 | °C |

Thermal Characteristics

| | | | |
|-----------------|---|-----|------|
| $R_{\theta JC}$ | Thermal Resistance, Junction to Case | 2.3 | °C/W |
| $R_{\theta JA}$ | Thermal Resistance, Junction to Ambient (Note 1a) | 40 | |

Package Marking and Ordering Information

| Device Marking | Device | Package | Reel Size | Tape Width | Quantity |
|----------------|------------|---------------|-----------|------------|------------|
| FDD86102LZ | FDD86102LZ | D-PAK(TO-252) | 13 " | 16 mm | 2500 units |

FDD86102LZ N-Channel Shielded Gate PowerTrench[®] MOSFET

Electrical Characteristics $T_J = 25\text{ }^\circ\text{C}$ unless otherwise noted

| Symbol | Parameter | Test Conditions | Min | Typ | Max | Units |
|--------|-----------|-----------------|-----|-----|-----|-------|
|--------|-----------|-----------------|-----|-----|-----|-------|

Off Characteristics

| | | | | | | |
|--------------------------------------|---|---|-----|----|----------|----------------------|
| BV_{DSS} | Drain to Source Breakdown Voltage | $I_D = 250\text{ }\mu\text{A}, V_{GS} = 0\text{ V}$ | 100 | | | V |
| $\frac{\Delta BV_{DSS}}{\Delta T_J}$ | Breakdown Voltage Temperature Coefficient | $I_D = 250\text{ }\mu\text{A}$, referenced to $25\text{ }^\circ\text{C}$ | | 69 | | mV/ $^\circ\text{C}$ |
| I_{DSS} | Zero Gate Voltage Drain Current | $V_{DS} = 80\text{ V}, V_{GS} = 0\text{ V}$ | | | 1 | μA |
| I_{GSS} | Gate to Source Leakage Current | $V_{GS} = \pm 20\text{ V}, V_{DS} = 0\text{ V}$ | | | ± 10 | μA |

On Characteristics (Note 2)

| | | | | | | |
|--|--|---|-----|------|------|----------------------|
| $V_{GS(th)}$ | Gate to Source Threshold Voltage | $V_{GS} = V_{DS}, I_D = 250\text{ }\mu\text{A}$ | 1.0 | 1.5 | 3.0 | V |
| $\frac{\Delta V_{GS(th)}}{\Delta T_J}$ | Gate to Source Threshold Voltage Temperature Coefficient | $I_D = 250\text{ }\mu\text{A}$, referenced to $25\text{ }^\circ\text{C}$ | | -6 | | mV/ $^\circ\text{C}$ |
| $r_{DS(on)}$ | Static Drain to Source On Resistance | $V_{GS} = 10\text{ V}, I_D = 8\text{ A}$ | | 17.8 | 22.5 | m Ω |
| | | $V_{GS} = 4.5\text{ V}, I_D = 7\text{ A}$ | | 23.2 | 31 | |
| | | $V_{GS} = 10\text{ V}, I_D = 8\text{ A}, T_J = 125\text{ }^\circ\text{C}$ | | 31.1 | 40 | |
| g_{FS} | Forward Transconductance | $V_{DS} = 5\text{ V}, I_D = 8\text{ A}$ | | 31 | | S |

Dynamic Characteristics

| | | | | | | |
|-----------|------------------------------|--|--|------|------|----------|
| C_{iss} | Input Capacitance | $V_{DS} = 50\text{ V}, V_{GS} = 0\text{ V},$ $f = 1\text{ MHz}$ | | 1157 | 1540 | pF |
| C_{oss} | Output Capacitance | | | 181 | 245 | pF |
| C_{rss} | Reverse Transfer Capacitance | | | 7.7 | 15 | pF |
| R_g | Gate Resistance | | | 0.6 | | Ω |

Switching Characteristics

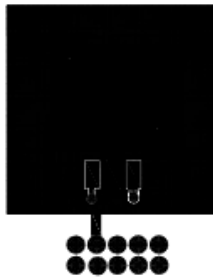
| | | | | | | |
|--------------|-------------------------------|--|---|-----|----|----|
| $t_{d(on)}$ | Turn-On Delay Time | $V_{DD} = 50\text{ V}, I_D = 8\text{ A},$ $V_{GS} = 10\text{ V}, R_{GEN} = 6\text{ }\Omega$ | | 6.6 | 14 | ns |
| t_r | Rise Time | | | 2.3 | 10 | ns |
| $t_{d(off)}$ | Turn-Off Delay Time | | | 20 | 32 | ns |
| t_f | Fall Time | | | 2.3 | 10 | ns |
| Q_g | Total Gate Charge | | $V_{GS} = 0\text{ V to } 10\text{ V}$ | | 18 | 26 |
| Q_g | Total Gate Charge | $V_{GS} = 0\text{ V to } 4.5\text{ V}$ | $V_{DD} = 50\text{ V},$ $I_D = 8\text{ A}$ | 8.7 | 13 | nC |
| Q_{gs} | Gate to Source Gate Charge | | | 2.7 | | nC |
| Q_{gd} | Gate to Drain "Miller" Charge | | | 2.4 | | nC |

Drain-Source Diode Characteristics

| | | | | | | |
|----------|---------------------------------------|--|--|------|-----|----|
| V_{SD} | Source to Drain Diode Forward Voltage | $V_{GS} = 0\text{ V}, I_S = 8\text{ A}$ (Note 2) | | 0.82 | 1.3 | V |
| | | $V_{GS} = 0\text{ V}, I_S = 2.6\text{ A}$ (Note 2) | | 0.75 | 1.2 | |
| t_{rr} | Reverse Recovery Time | $I_F = 8\text{ A}, di/dt = 100\text{ A}/\mu\text{s}$ | | 43 | 70 | ns |
| Q_{rr} | Reverse Recovery Charge | | | 43 | 70 | nC |

Notes:

- $R_{\theta JA}$ is the sum of the junction-to-case and case-to-ambient thermal resistance where the case thermal reference is defined as the solder mounting surface of the drain pins. $R_{\theta JC}$ is guaranteed by design while $R_{\theta JA}$ is determined by the user's board design.



a. $40\text{ }^\circ\text{C/W}$ when mounted on a 1 in^2 pad of 2 oz copper.



b. $96\text{ }^\circ\text{C/W}$ when mounted on a minimum pad of 2 oz copper.

2. Pulse Test: Pulse Width < $300\text{ }\mu\text{s}$, Duty cycle < 2.0%.

3. Starting $T_J = 25\text{ }^\circ\text{C}$, $L = 1\text{ mH}$, $I_{AS} = 13\text{ A}$, $V_{DD} = 90\text{ V}$, $V_{GS} = 10\text{ V}$.

4. The diode connected between the gate and source serves only as protection against ESD. No gate overvoltage rating is implied.

Typical Characteristics $T_J = 25\text{ }^\circ\text{C}$ unless otherwise noted

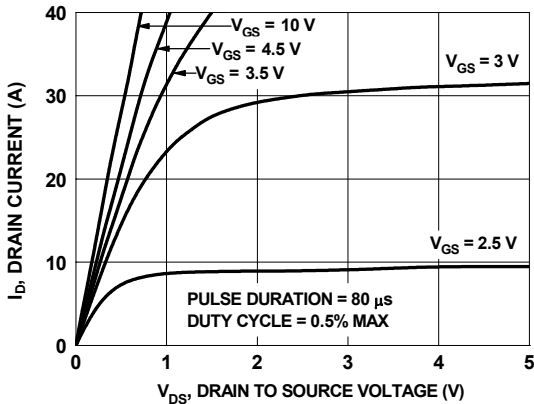


Figure 1. On-Region Characteristics

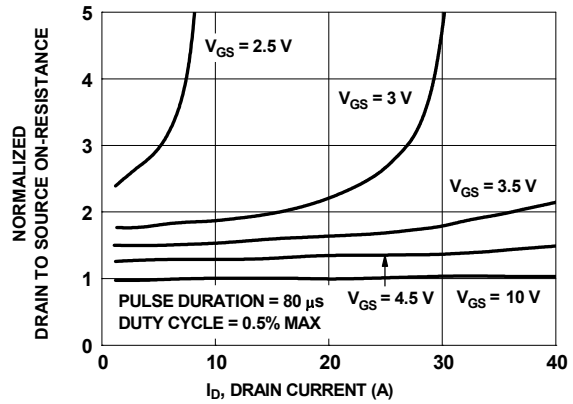


Figure 2. Normalized On-Resistance vs Drain Current and Gate Voltage

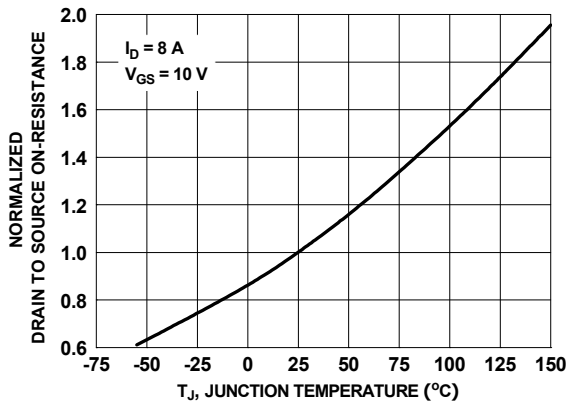


Figure 3. Normalized On-Resistance vs Junction Temperature

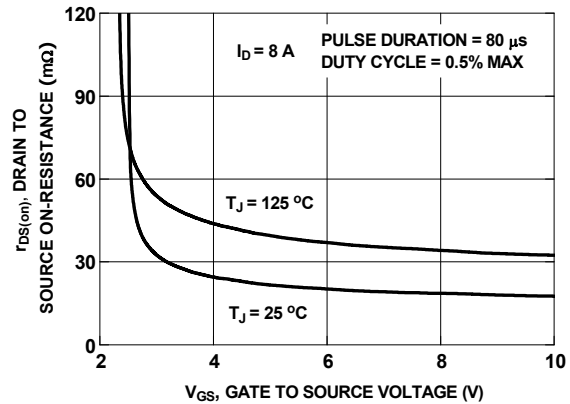


Figure 4. On-Resistance vs Gate to Source Voltage

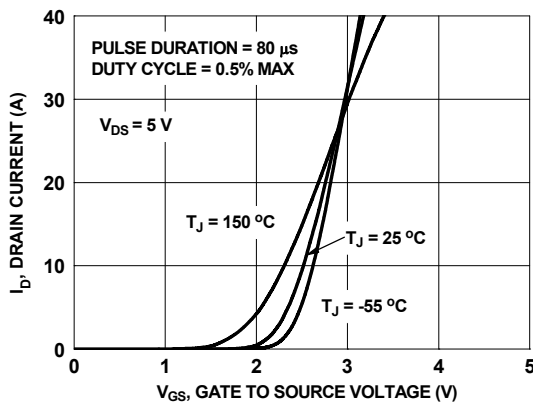


Figure 5. Transfer Characteristics

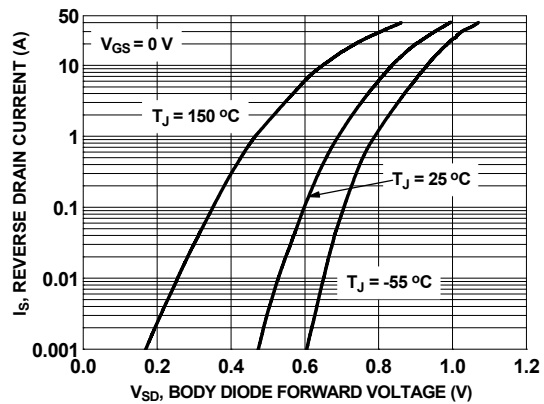


Figure 6. Source to Drain Diode Forward Voltage vs Source Current

Typical Characteristics $T_J = 25\text{ }^\circ\text{C}$ unless otherwise noted

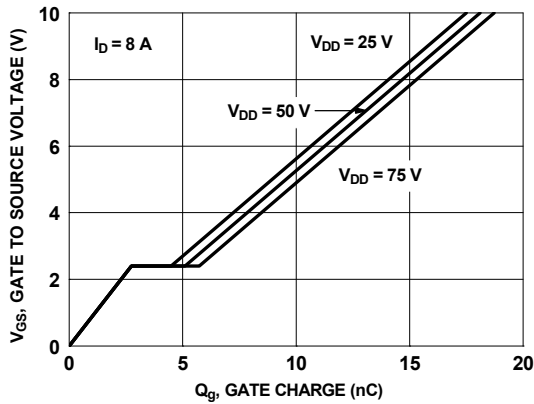


Figure 7. Gate Charge Characteristics

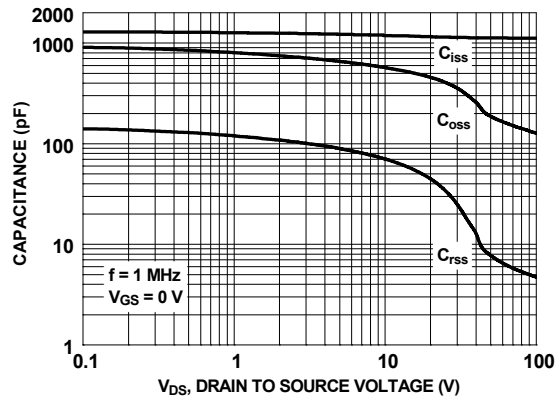


Figure 8. Capacitance vs Drain to Source Voltage

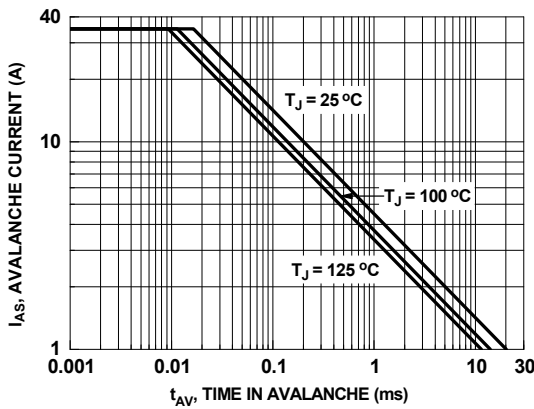


Figure 9. Unclamped Inductive Switching Capability

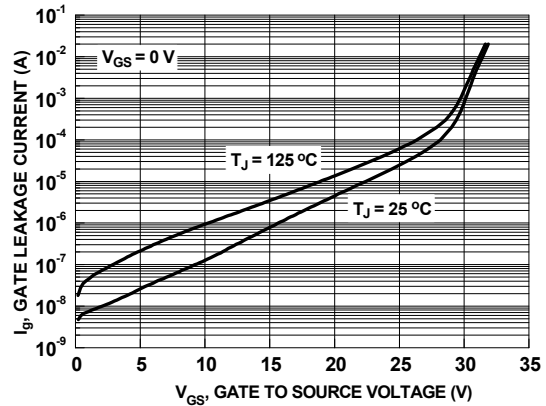


Figure 10. Gate Leakage Current vs Gate to Source Voltage

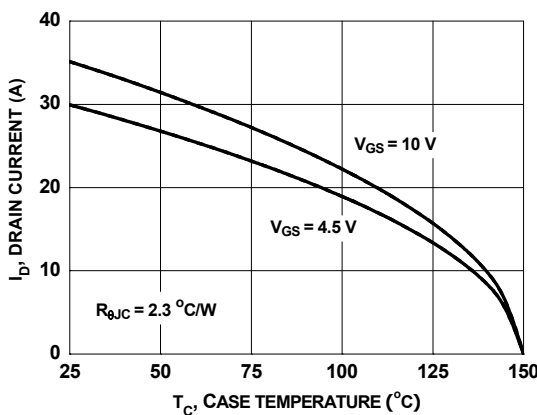


Figure 11. Maximum Continuous Drain Current vs Case Temperature

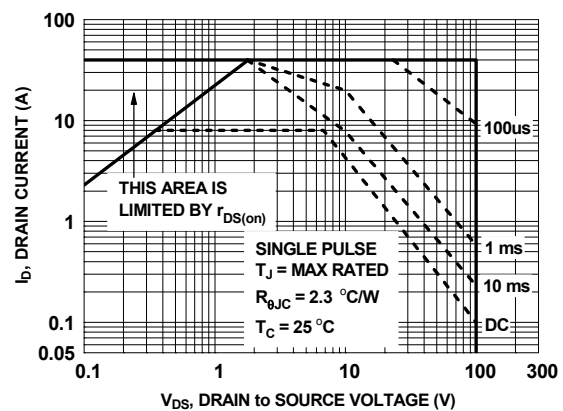


Figure 12. Forward Bias Safe Operating Area

Typical Characteristics $T_J = 25\text{ }^\circ\text{C}$ unless otherwise noted

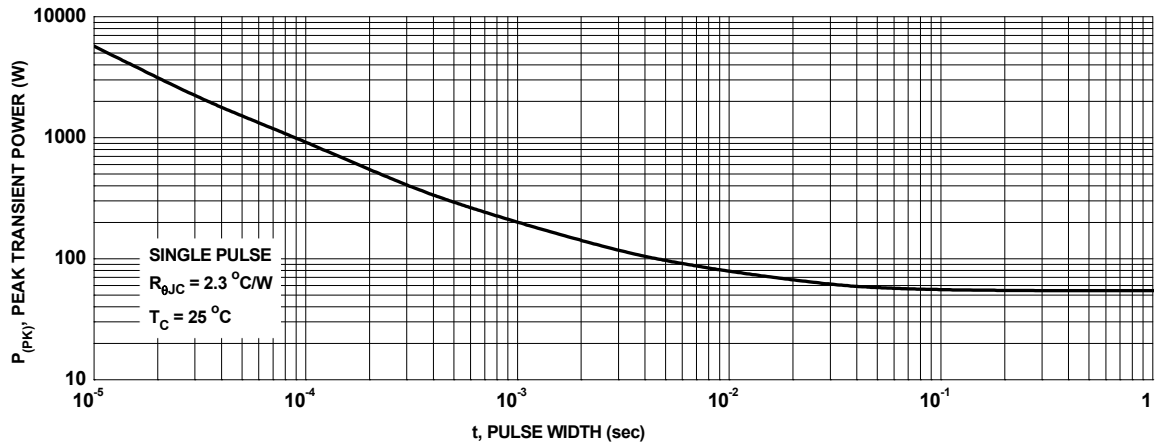


Figure 13. Single Pulse Maximum Power Dissipation

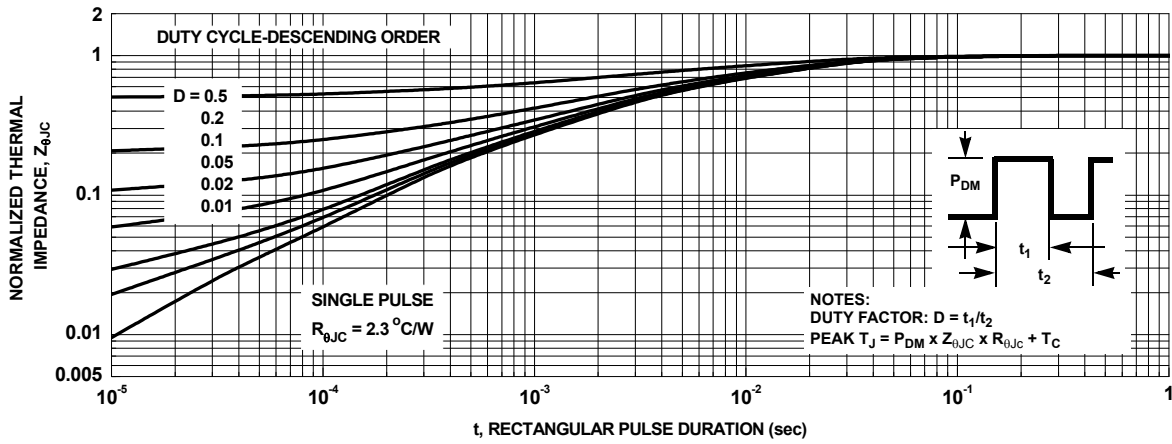
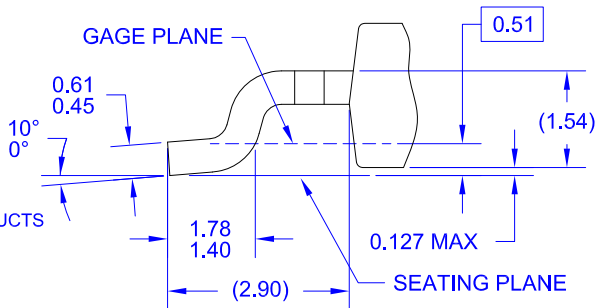


Figure 14. Junction-to-Case Transient Thermal Response Curve



NOTES: UNLESS OTHERWISE SPECIFIED

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- B) ALL DIMENSIONS ARE IN MILLIMETERS.
- C) DIMENSIONING AND TOLERANCING PER ASME Y14.5M-2009.
- D) SUPPLIER DEPENDENT MOLD LOCKING HOLES OR CHAMFERED CORNERS OR EDGE PROTRUSION.
- E) TRIMMED METAL CENTER LEAD IS PRESENT ON FOR NON-DIODE PRODUCTS
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- H) DRAWING NUMBER AND REVISION: MKT-TO252A03REV11



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